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Texas Instruments
CSD16340Q3

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Datasheet of CSD16340Q3 - MOSFET N-CH 25V 60A 8SON

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CSD16340Q3

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CSD16340Q3 25-V N-Channel NexFET™ Power MOSFET

1 Features

- · Optimized for 5 V Gate Drive
- Resistance Rated at V_{GS} =2.5 V
- Ultra-Low Q_q and Q_{qd}
- · Low Thermal Resistance
- · Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 3.3-mm × 3.3-mm Plastic Package

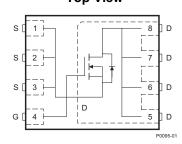
2 Applications

- Point of Load Synchronous Buck Converter for Applications in Networking, Telecom, and Computing Systems
- Optimized for Control or Synchronous FET Applications

3 Description

This 25 V, 3.8 m Ω , 3.3 x 3.3 mm SON NexFETTM power MOSFET is designed to minimize losses in power conversion and optimized for 5 V gate drive applications.

Top View



$R_{DS(on)}$ vs V_{GS} 16 R_{DS(on)} - On-State Resistance - mΩ 14 I_D = 20Å 12 10 8 T_{C} = 125°C 6 = 25°C 2 0 0 1 5 8 10 V_{GS} - Gate to Source Voltage - V G006

Product Summary

T _A = 25°C		VALUE		UNIT
V_{DS}	Drain-to-Source Voltage 25			V
Q_g	Gate Charge Total (4.5 V)	6.5		nC
Q_{gd}	Gate Charge Gate-to-Drain 1.2		nC	
		$V_{GS} = 2.5 \text{ V}$	6.1	mΩ
R _{DS(on)}	Drain-to-Source On-Resistance	$V_{GS} = 4.5 \text{ V}$	4.3	mΩ
		V _{GS} = 8 V	3.8	mΩ
V_{th}	V _{th} Threshold Voltage			V

Ordering Information⁽¹⁾

Device	Media	Qty	Package	Ship
CSD16340Q3	13-Inch Reel	2500	SON 3.3 x 3.3 mm	Tape and
CSD16340Q3T	7-Inch Reel	250	Plastic Package	Reel

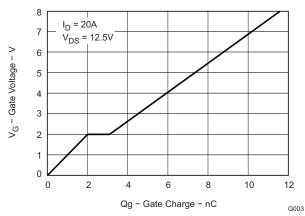
(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

T _A = 2	5°C	VALUE	UNIT
V _{DS}	Drain-to-Source Voltage	25	V
V_{GS}	Gate-to-Source Voltage	+10 / -8	V
	Continuous Drain Current, T _C = 25°C	60	Α
I _D	Continuous Drain Current ⁽¹⁾	21	Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	115	Α
P_D	Power Dissipation ⁽¹⁾	3	W
T _J , T _{stg}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse $I_D = 40 \text{ A}, L = 0.1 \text{ mH}, R_G = 25 \Omega$	80	mJ

- (1) Typical $R_{\theta JA} = 39^{\circ} \text{C/W}$ on $1 \text{in}^2 \text{ Cu}$ (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width ≤300 µs, duty cycle ≤2%

Gate Charge



A



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	Revision History		Page
6	Device and Documentation Support 8		7.4 Q3 Tape and Reel Information 11
	5.1 Electrical Characteristics		7.2 Recommended PCB Pattern
4 5	Revision History	7	Mechanical, Packaging, and Orderable Information
1 2 3	Features 1 Applications 1 Description 1		6.1 Trademarks

•	Added 7" reel to Ordering Information	·

•	Added 7" reel to Ordering Information	1
•	Updated Mechanical Information	9

Changes from Revision C (June 2011) to Revision D

•	Replaced the THERMAL CHARACTERISTICS table with the new Thermal Information Table	4
•	Replaced Figure 10 - Maximum Safe Operating Area	6

Changes from Revision B (September 2010) to Revision C

Page

|--|

Changes from Revision A (January 2010) to Revision B

Changed Figure 2, reversed the order of the V _{GS} labels	. 5
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Changes from Original (December 2009) to Revision A

Page

Page

•	Changed Q	in the PRODUCT	SUMMARY	table from: 6.8	To 6.5 nC.
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5 Specifications

5.1 Electrical Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC	CHARACTERISTICS					
BV _{DSS}	Drain-to-Source Voltage	V _{GS} = 0 V, I _{DS} = 250 μA	25			V
I _{DSS}	Drain-to-Source Leakage Current	V _{GS} = 0 V, V _{DS} = 20 V			1	μΑ
I _{GSS}	Gate-to-Source Leakage Current	V _{DS} = 0 V, V _{GS} = +10/-8 V			100	nA
V _{GS(th)}	Gate-to-Source Threshold Voltage	$V_{DS} = V_{GS}$, $I_{DS} = 250 \mu A$	0.6	0.85	1.1	V
R _{DS(on)}		V _{GS} = 2.5 V, I _{DS} = 20 A		6.1	7.8	mΩ
	Drain-to-Source On-Resistance	V _{GS} = 4.5 V, I _{DS} = 20 A		4.3	5.5	mΩ
		V _{GS} = 8 V, I _{DS} = 20 A		3.8	4.5	mΩ
g_{fs}	Transconductance	V _{DS} = 15 V, I _{DS} = 20 A		121		S
DYNAMI	C CHARACTERISTICS				,	
C _{ISS}	Input Capacitance			1050	1350	pF
Coss	Output Capacitance	V _{GS} = 0 V, V _{DS} = 12.5 V, f = 1 MHz		730	950	pF
C _{RSS}	Reverse Transfer Capacitance			53	69	pF
R_g	Series Gate Resistance			1.5	3	Ω
Qg	Gate Charge Total (4.5 V)			6.5	9.2	nC
Q _{gd}	Gate Charge Gate-to-Drain	V 42.5.V L 20.A		1.2		nC
Q _{gs}	Gate Charge Gate-to-Source	V _{DS} = 12.5 V, I _D = 20 A		2.1		nC
Qg(th)	Gate Charge at V _{th}			1		nC
Q _{OSS}	Output Charge	V _{DS} = 13 V, V _{GS} = 0 V	1			nC
t _{d(on)}	Turn On Delay Time			4.8		ns
t _r	Rise Time	V _{DS} = 12.5 V, V _{GS} = 4.5 V, I _D = 20 A		16.1		ns
t _{d(off)}	Turn Off Delay Time	$R_G = 2 \Omega$		13.8		ns
t_f	Fall Time			5.2		ns
DIODE C	CHARACTERISTICS				,	
V _{SD}	Diode Forward Voltage	I _S = 20 A, V _{GS} = 0 V	0.8		1	V
Q _{rr}	Reverse Recovery Charge	V 40 V 1 00 A 17/1 000 C		14.5		nC
t _{rr}	Reverse Recovery Time	$V_{DD} = 13 \text{ V}, I_F = 20 \text{ A}, \text{ di/dt} = 300 \text{ A/}\mu\text{s}$		20		ns

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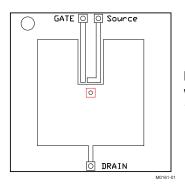
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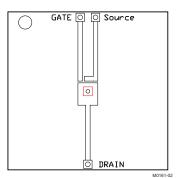
5.2 Thermal Information

	THERMAL METRIC ⁽¹⁾⁽²⁾	CSD16340Q3	LINUTO
	THERMAL METRIC	Q3 (8 PINS)	UNITS
θ_{JA}	Junction-to-Ambient Thermal Resistance	42.0	
θ_{JCtop}	Junction-to-Case (top) Thermal Resistance	20.6	
θ_{JB}	Junction-to-Board Thermal Resistance	8.8	°C/W
ΨЈТ	Junction-to-Top Characterization Parameter	0.3	*C/VV
ΨЈВ	Junction-to-Board Characterization Parameter	8.7	
θ_{JCbot}	Junction-to-Case (bottom) Thermal Resistance	0.1	

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.
 (2) For thermal estimates of this device based on PCB copper area, see the TI PCB Thermal Calculator.



Max $R_{\theta JA} = 58^{\circ}C/W$ when mounted on 1 inch² of 2 oz. Cu.



Max $R_{\theta JA} = 162^{\circ}C/W$ when mounted on minimum pad area of 2 oz. Cu.

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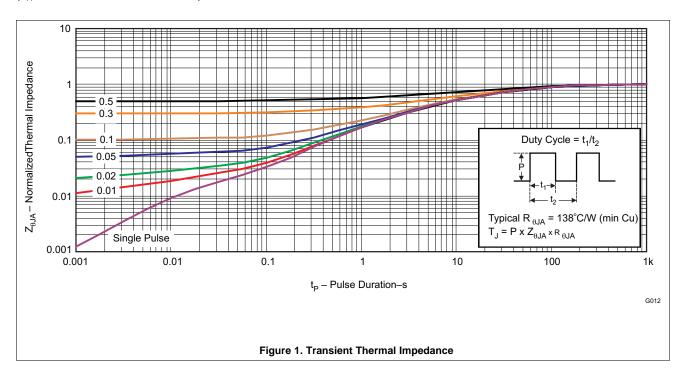
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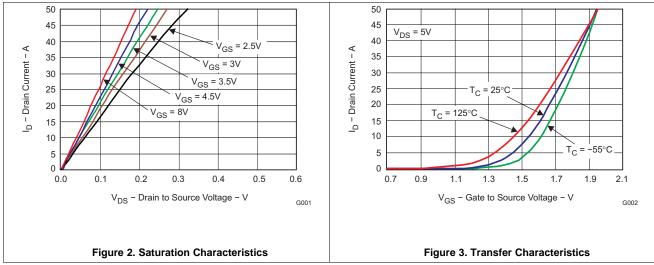
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5.3 Typical MOSFET Characteristics

(T_A = 25°C unless otherwise stated)





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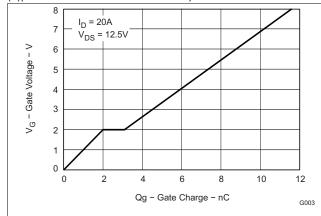
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Typical MOSFET Characteristics (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$



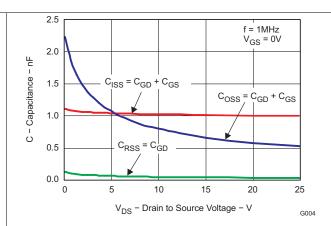


Figure 4. Gate Charge

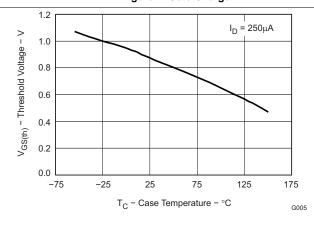


Figure 5. Capacitance

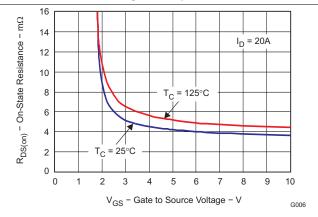


Figure 6. Threshold Voltage vs Temperature

Figure 7. On-Resistance vs Gate Voltage

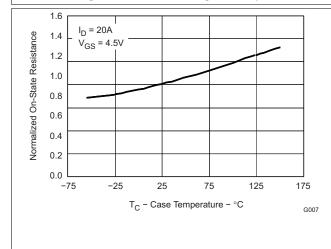


Figure 8. Normalized On Resistance vs Temperature

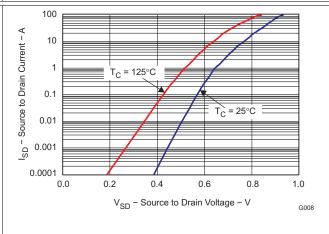


Figure 9. Typical Diode Forward Voltage

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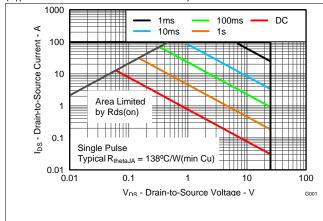
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Typical MOSFET Characteristics (continued)

(T_A = 25°C unless otherwise stated)



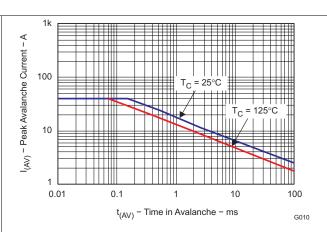


Figure 10. Maximum Safe Operating Area

Figure 11. Single Pulse Unclamped Inductive Switching

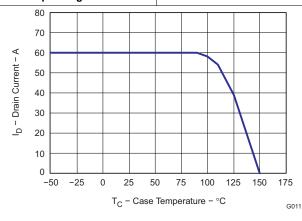


Figure 12. Maximum Drain Current vs Temperature

Product Folder Links: CSD16340Q3



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6 Device and Documentation Support

6.1 Trademarks

NexFET is a trademark of Texas Instruments.

6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

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6.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

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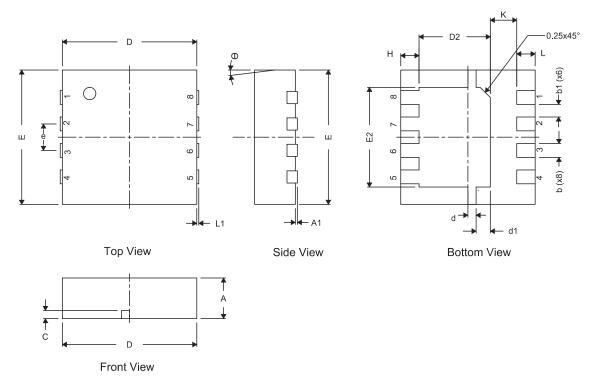
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7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Q3 Package Dimensions



DIM		MILLIMETERS	3	INCHES				
DIM	MIN	NOM	MAX	MIN	NOM	MAX		
Α	0.950	1.000	1.100	0.037	0.039	0.043		
A1	0.000	0.000	0.050	0.000	0.000	0.002		
b	0.280	0.340	0.400	0.011	0.013	0.016		
b1		0.310 NOM		0.012 NOM				
С	0.150	0.200	0.250	0.006	0.008	0.010		
D	3.200	3.300	3.400	0.126	0.130	0.134		
D2	1.650	1.750	1.800	0.065	0.069	0.071		
d	0.150	0.200	0.250	0.006	0.008	0.010		
d1	0.300	0.350	0.400	0.012	0.014	0.016		
Е	3.200	3.300	3.400	0.126	0.130	0.134		
E2	2.350	2.450	2.550	0.093	0.096	0.100		
е		0.650 TYP		0.026				
Н	0.35 0.450		0.550	0.014	0.018	0.022		
K		0.650 TYP		0.026 TYP				
L	0.35	0.450	0.550	0.014	0.018	0.022		
L1	0	_	0	0	_	0		
θ	0	_	0	0		0		

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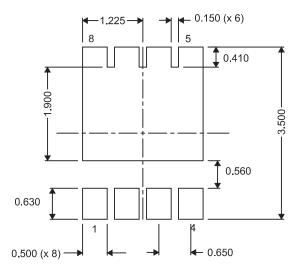


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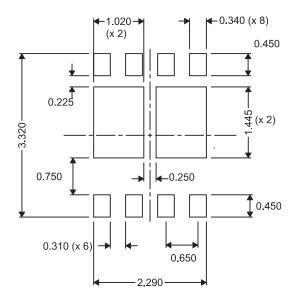
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7.2 Recommended PCB Pattern



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

7.3 Recommended Stencil Opening



All dimensions are in mm, unless otherwise specified.

10

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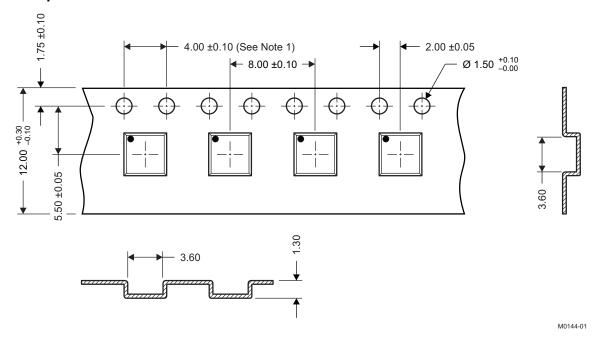


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7.4 Q3 Tape and Reel Information



Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm
- 3. Material: black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified).
- 5. Thickness: 0.30 ±0.05 mm
- 6. MSL1 260°C (IR and Convection) PbF-Reflow Compatible

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PACKAGE OPTION ADDENDUM

7-Jan-2016

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins Pac	ckage	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing	0	Qty	(2)	(6)	(3)		(4/5)	
CSD16340Q3	ACTIVE	VSON-CLIP	DQG	8 2	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD16340	Samples
CSD16340Q3T	ACTIVE	VSON-CLIP	DQG	8 2	250	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD16340	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design. PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): Tl's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width

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PACKAGE OPTION ADDENDUM

INSTRUMENTS

7-Jan-2016

In no event shall TTs liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

Addendum-Page 2



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